

NTE937M Integrated Circuit JFET Input Operational Amplifier

Description:

The NTE937M is a monolithic JFET input operational amplifier in an 8–Lead DIP type package incorporating well–matched, high voltage JFET's on the same chip with standard bi–polar transistors. This amplifier features low input bias and offset currents, low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common–mode rejection. It is also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Advantages:

- Replaces Expensive Hybrid and Module FET OP Amps
- Rugged JFET's Allow Blow-Out Free Handling Compared with MOSFET Input Device
- Excellent for Low Noise Applications using either High or Low Source Impedance Very Low 1/f Corner
- Offset Adjust does not Degrade Drift or Common–Mode Rejection as in Most Monolithic Amplifiers
- New Output Stage Allows use of Large Capacitive Loads (10,000pF) without Stability Problems
- Internal Compensation and Large Differential Input Voltage Capability

Applications:

- Precision High Speed Integrators
- Fast D/A and A/D Converters
- High Impedance Buffers
- Wideband, Low Noise, Low Drift Amplifiers
- Logarithmic Amplifiers
- Photocell Amplifiers
- Sample and Hold Circuits

Absolute Maximum Ratings:

Supply Voltage	±18V
Maximum Power Dissipation (at +25°C, Note 1), P _d	500mW
Differential Input Voltage	±30V
Input Voltage Range (Note 2)	±16V
Output Short–Circuit Duration	Continuous
Maximum Operating Junction Temperature (Note 1), T _J max	+100°C
Storage Temperature Range, T _{stg}	. –65° to +150°C
Lead Temperature (During Soldering, 10sec), T _L	+300°C
Thermal Resistance, Junction–to–Ambient (Note 1), R _{thJC}	+155°C/W

- Note 1. The maximum power dissipation for this device must be derated at elevated temperatures and is dictated by T_J max, R_{thJC} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_d = (T_J$ max $T_A)/R_{thJC}$ or the +25°C P_d max, whichever is less.
- Note 2. Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply voltage.

DC Electrical Characteristics: $(T_A = +25C, V_S = \pm 15V \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Supply Current	I _{CC}		_	5	10	mA

<u>DC Electrical Characteristics:</u> $(V_S = \pm 15V, \, 0^\circ \le T_A \le +70^\circ C, \, T_{HIGH} = +70^\circ C \, unles \, otherwise \, specified)$

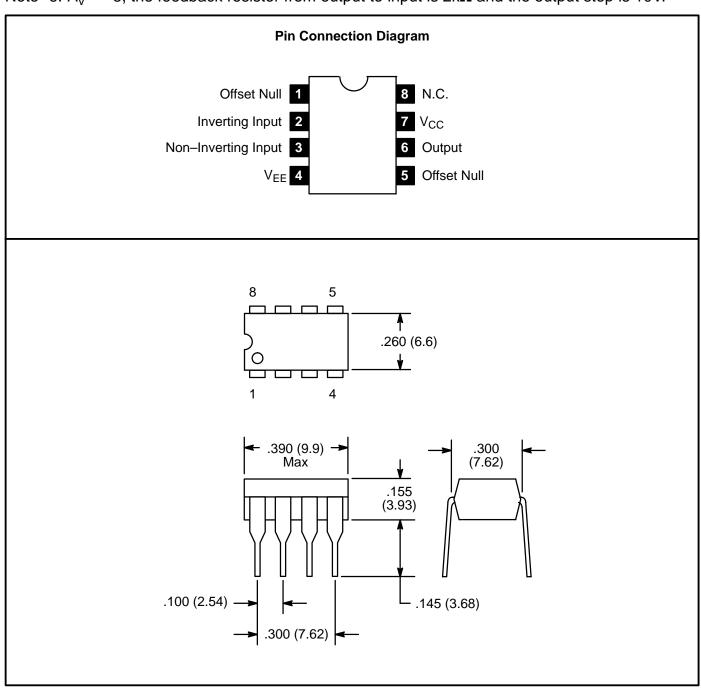
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Input Offset Voltage	Vos	$R_S = 50\Omega, T_A = +25^{\circ}C$	_	3	10	mV	
		Over Temperature	_	_	13	mV	
Average TC of Input Offset Voltage	$\Delta V_{OS}/\Delta T$	$R_S = 50\Omega$ – 5 –					
Change in Average TC with V _{OS} Adjust	ΔTC/ΔV _{OS}	$R_S = 50\Omega$, Note 3	0.5	_	μV/°C		
Input Offset Current	Ios	$T_J = +25^{\circ}C$, Note 4	_	3	50	pА	
		$T_J \le T_{HIGH}$	_	_	2	nA	
Input Bias Current	Ι _Β	$T_J = +25^{\circ}C$, Note 4	_	30	200	рА	
		$T_J \le T_{HIGH}$	_	_	8	nA	
Input Resistance	R _{IN}	$T_J = +25^{\circ}C$	_	10 ¹²	_	Ω	
Large Signal Voltage Gain	A _{VOL}	$T_A = +25$ °C, $V_O = \pm 10$ V, $R_L = 2$ k	25	200	_	V/mV	
		Over Temperature	15	_	_	V/mV	
Output Voltage Swing	Vo	R _L = 10k	±12	±13	_	V	
		$R_L = 2k$	±10	±12	_	V	
Input Common–Mode Voltage Range	V _{CM}		±10	+15.1 -12	_	V	
Common–Mode Rejection Ratio	CMRR		_	80	100	dB	
Supply Voltage Rejection Ratio	PSRR	Note 5 – 80 100				dB	

- Note 3. The temperature coeficient of the adjust input offset voltage changes only a small amount (0.5μV/°C typically) for each mV of adjustment from its original unadjusted value. Common—mode rejection and open loop voltage gain are also unaffected by offset adjustment.
- Note 4. The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_J. Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, P_d. T_J = T_A + R_{thJC} P_d where R_{thJC} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.
- Note 5. Supply Voltage Rejection is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

<u>AC Electrical Characteristics:</u> $(T_A = +25C, V_S = \pm 15V \text{ unless otherwise specified)}$

Parameter	Symbol	Test Co	Min	Тур	Max	Unit	
Slew Rate	SR	$A_V = 5$		30	50	_	V/µs
Gain Bandwidth Product	GBW		_	20	_	MHz	
Settling Time to 0.01%	ts	Note 6	_	1.5	_	μs	
Equivalent Input Noise Voltage	e _N	$R_S = 100\Omega$	f = 100Hz	_	15	_	nV/√ Hz
			f = 1000Hz	_	12	_	nV/√ Hz
Equivalent Input Current Noise	i _N	f = 100Hz f = 1000Hz		_	0.01	_	pA/√Hz
				_	0.01	_	pA/√ Hz
Input Capacitance	C _{IN}			_	3	_	pF

Note 6. $A_V = -5$, the feedback resistor from output to input is $2k\Omega$ and the output step is 10V.



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